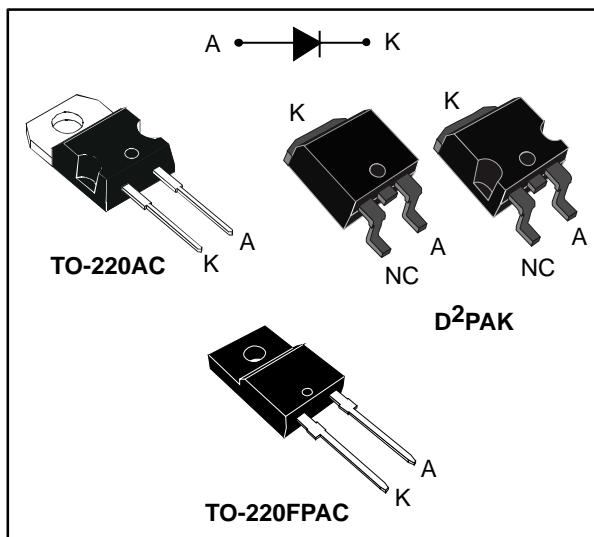




STPS8H100

High voltage power Schottky rectifier

Datasheet - production data



Features

- Negligible switching losses
- High junction temperature capability
- Low leakage current
- Good trade off between leakage current and forward voltage drop
- Insulated package:
 - TO-220FPAC, insulating voltage = 2000 V_{RMS} sine
- Avalanche capability specified
- ECOPACK®2 compliant component for D²PAK on demand

Description

Schottky barrier rectifier designed for high frequency compact switched mode power supplies such as adaptors and on-board DC-DC converters.

Table 1: Device summary

Symbol	Value
I _{F(AV)}	8 A
V _{RRM}	100 V
T _j (max)	175 °C
V _F (typ)	0.56 V

1 Characteristics

Table 2: Absolute ratings (limiting values, at 25 °C, unless otherwise specified)

Symbol	Parameter			Value	Unit	
V _{RRM}	Repetitive peak reverse voltage			100	V	
I _{F(RMS)}	Forward rms current			30	A	
I _{F(AV)}	Average forward current $\delta = 0.5$, square wave	TO-220AC, D ² PAK	T _C = 165 °C	8	A	
		TO-220FPAC	T _C = 150 °C			
I _{FSM}	Surge non repetitive forward current	tp = 10 ms sinusoidal			250 A	
P _{ARM}	Repetitive peak avalanche power	tp = 10 µs, T _j = 125 °C			750 W	
T _{stg}	Storage temperature range			-65 to + 175	°C	
T _j	Maximum operating junction temperature ⁽¹⁾			+ 175	°C	

Notes:

⁽¹⁾(dP_{tot}/dT_j) < (1/R_{th(j-a)}) condition to avoid thermal runaway for a diode on its own heatsink.

Table 3: Thermal parameter

Symbol	Parameter		Value	Unit
R _{th(j-c)}	Junction to case	TO-220AC, D ² PAK	1.6	°C/W
		TO-220FPAC	4	

Table 4: Static electrical characteristics

Symbol	Parameter	Test conditions		Min.	Typ.	Max.	Unit
I _R ⁽¹⁾	Reverse leakage current	T _j = 25 °C	V _R = V _{RRM}	-		4.5	µA
		T _j = 125 °C		-	2.0	6.0	mA
V _F ⁽²⁾	Forward voltage drop	T _j = 25 °C	I _F = 8 A	-		0.71	V
		T _j = 125 °C		-	0.56	0.58	
		T _j = 25 °C	I _F = 10 A	-		0.77	
		T _j = 125 °C		-	0.59	0.64	
		T _j = 25 °C	I _F = 16 A	-		0.81	
		T _j = 125 °C		-	0.65	0.68	

Notes:

⁽¹⁾Pulse test: t_p = 5 ms, δ < 2%

⁽²⁾Pulse test: t_p = 380 µs, δ < 2%

To evaluate the conduction losses use the following equation:

$$P = 0.48 \times I_{F(AV)} + 0.0125 I_{F^2(RMS)}$$

1.1 Characteristics (curves)

Figure 1: Average forward power dissipation versus average forward current

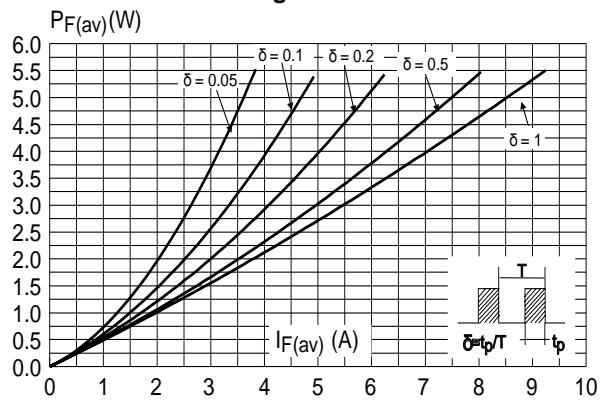


Figure 2: Normalized avalanche power derating versus pulse duration ($T_j= 125^\circ\text{C}$)

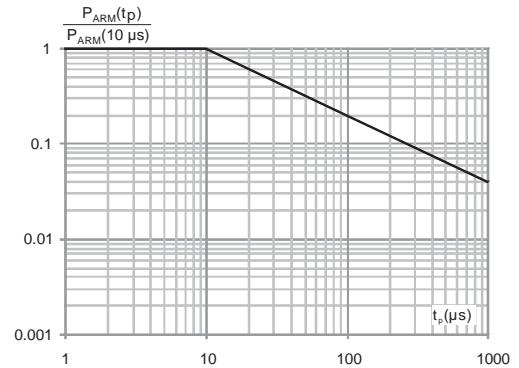


Figure 3: Average forward current versus ambient temperature, $\delta = 0.5$ (TO-220AC, D²PAK)

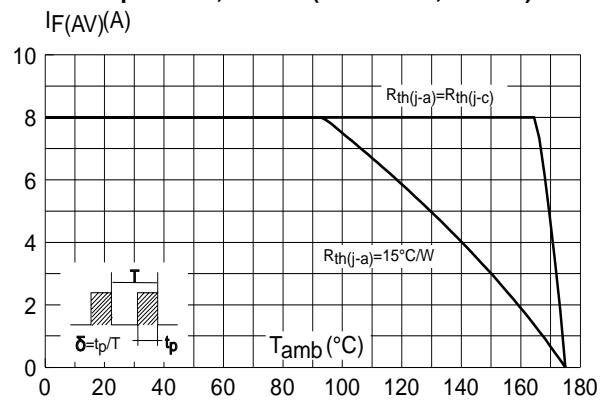


Figure 4: Average forward current versus ambient temperature, $\delta = 0.5$ (TO-220FPAC)

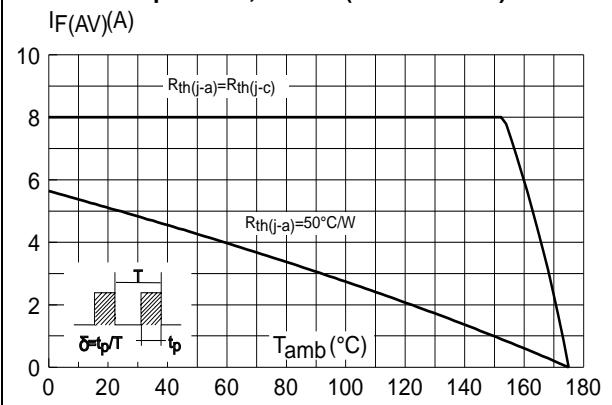


Figure 5: Relative variation of thermal impedance junction to case versus pulse duration (TO-220AC, D²PAK)

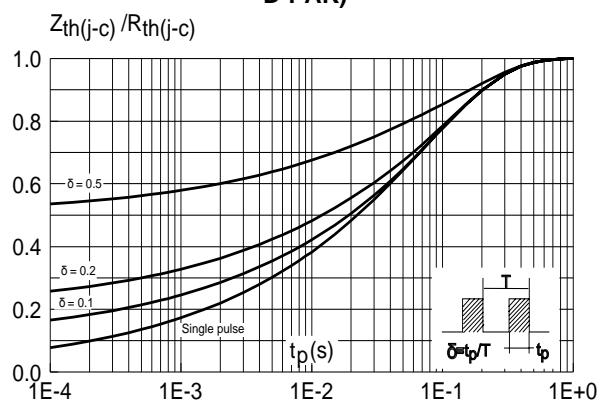


Figure 6: Relative variation of thermal impedance junction to case versus pulse duration (TO-220FPAC)

